
ABSTRACT OF THE DISCLOSURE

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A semiconductor device comprising a semiconductor layer having at least first and second impurity regions and a channel formation region formed on an insulating surface; a gate insulating film adjacent to the semiconductor layer; a gate electrode adjacent to the gate insulating film; a first insulating film formed over the insulating surface, the semiconductor layer, the gate insulating film and the gate electrode; a second insulating film comprising an organic resin formed on the first insulating film; an electrode formed over the second insulating film and connected to the one of the first and second impurity regions; and a pixel electrode formed over the second insulating film.
